N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

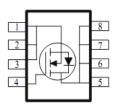
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
30	8 @ V _{GS} = 10V	17	
30	$11.5 @ V_{GS} = 4.5V$	15	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage	V_{DS}	30	V				
Gate-Source Voltage		V_{GS}	±20	V			
Continuous Drain Current a	T _A =25°C		17				
Continuous Drain Current	T _A =70°C	I _D	13	A			
Pulsed Drain Current ^b		I _{DM}	68				
Continuous Source Current (Diode Conduction) a		I _S	4.3	Α			
Power Dissipation ^a	T _A =25°C	P_{D}	3.5	W			
Power dissipation	T _A =70°C	l 'D	2	V V			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
Maximum Junction-to-Ambient	Steady State	IXOJA	81	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

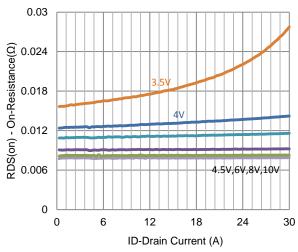
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	· uA	
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 13.3 \text{ A}$			8	mΩ	
Dialii-Source Oil-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10.6 \text{ A}$			11.5	mu	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 13.3 \text{ A}$		18		S	
Diode Forward Voltage	V_{SD}	$I_S = 2.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.71		V	
		Dynamic					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		15			
Gate-Source Charge	Q_{gs}	$I_{DS} = 13 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 13.3 \text{ A}$		5.6		nC	
Gate-Drain Charge	Q_gd	1g = 15.5 A		7.0			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_{L} = 1.1 \Omega,$		6			
Rise Time	t _r	$V_{DS} = 13 \text{ V}, K_L - 1.1 \Omega,$ $I_D = 13.3 \text{ A},$		15		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		38		ns	
Fall Time	t _f	VGEN = 10 V, NGEN = 0 12		20			
Input Capacitance	C _{iss}			1456			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		231		pF	
Reverse Transfer Capacitance	C_{rss}			198			

Notes

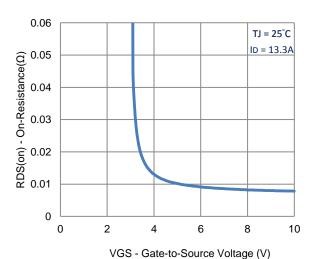
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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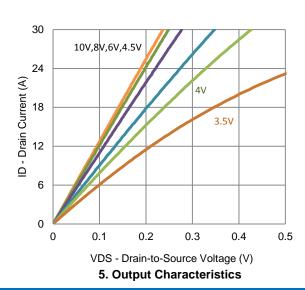
Typical Electrical Characteristics

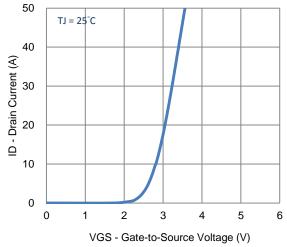


1. On-Resistance vs. Drain Current

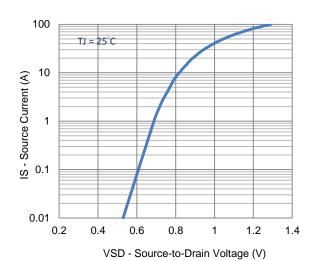


3. On-Resistance vs. Gate-to-Source Voltage

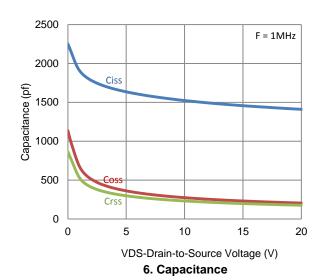




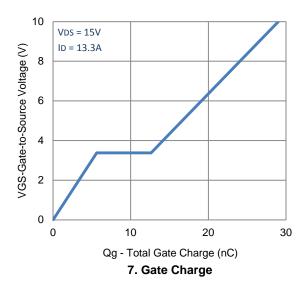
2. Transfer Characteristics

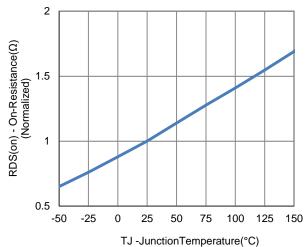


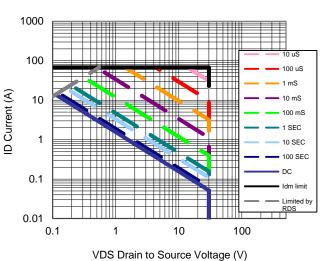
4. Drain-to-Source Forward Voltage



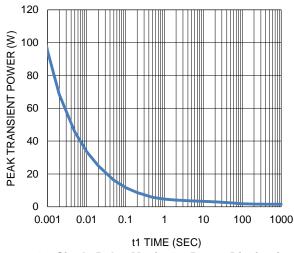
Typical Electrical Characteristics





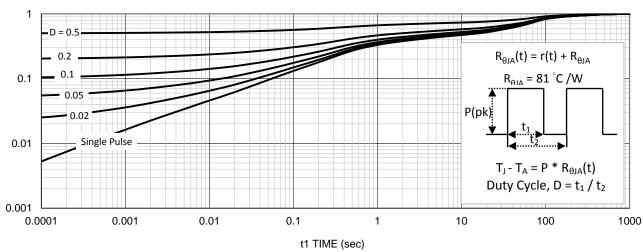


8. Normalized On-Resistance Vs Junction Temperature



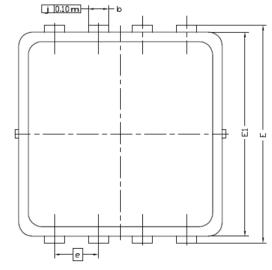
9. Safe Operating Area

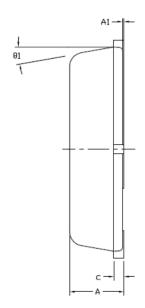
10. Single Pulse Maximum Power Dissipation

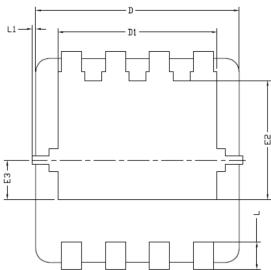


11. Normalized Thermal Transient Junction to Ambient

Package Information







птм	MILLIMETERS			INCHES			
DIM,	NIM	NDM	MAX	MIN	NDM	MAX	
Α	0,700	0,80	0.900	0,0276	0,0315	0.0354	
A1	0.00		0,05	0,000		0'005	
b	0.24	0.30	0.35	0.009	0.012	0.014	
С	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 B2C			0.118 BSC			
D1	2,35 BSC			0.093 BSC			
Ε	3.20 BSC			0,126 BSC			
E1	3.00 B2C			0.118 BSC			
E2	1.75 BSC			0.069 BSC			
E3	0,575 BSC			0.023 BSC			
е	0.65 BSC			0.026 B2C			
L	0,30	0,40	0,50	0,0118	0,0157	0,0197	
L1	0	1	0.100	0	-	0,004	
91	0°	10°	12*	0.	10°	12°	